## ST 2SC3330

## NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into five groups, $\mathrm{R}, \mathrm{O}, \mathrm{Y}$, $G$ and L , according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings $\left(\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}\right)$

|  | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector Base Voltage | $\mathrm{V}_{\text {CBO }}$ | 60 | V |
| Collector Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 50 | V |
| Emitter Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 5 | V |
| Collector Current | $\mathrm{I}_{\mathrm{C}}$ | 200 | mA |
| Power Dissipation | $\mathrm{P}_{\text {tot }}$ | 300 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{S}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$

|  | Symbol | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| DC Current Gain $\text { at } \mathrm{V}_{\mathrm{CE}}=6 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}$ |  |  |  |  |  |
| Current Gain Group R | $\mathrm{h}_{\mathrm{FE}}$ | 40 | - | 80 | - |
| $\bigcirc$ | $h_{\text {FE }}$ | 70 | - | 140 | - |
| Y | $h_{\text {FE }}$ | 120 | - | 240 | - |
| G | $h_{\text {FE }}$ | 200 | - | 400 | - |
| L | $\mathrm{h}_{\text {FE }}$ | 350 | - | 700 | - |
| Collector Base Breakdown Voltage at $\mathrm{I}_{\mathrm{C}}=100 \mu \mathrm{~A}$ | $\mathrm{V}_{\text {(BR) } \text { cbo }}$ | 60 | - | - | V |
| Collector Emitter Breakdown Voltage at $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}$ | $\mathrm{V}_{\text {(BR)CEO }}$ | 50 | - | - | V |
| Emitter Base Breakdown Voltage at $\mathrm{I}_{\mathrm{E}}=10 \mu \mathrm{~A}$ | $\mathrm{V}_{(\mathrm{BR}) \text { EbO }}$ | 5 | - | - | V |
| Collector Cutoff Current at $\mathrm{V}_{\mathrm{CB}}=40 \mathrm{~V}$ | $\mathrm{I}_{\text {cbo }}$ | - | - | 0.1 | $\mu \mathrm{A}$ |
| Emitter Cutoff Current at $\mathrm{V}_{\mathrm{EB}}=3 \mathrm{~V}$ | $\mathrm{I}_{\text {ebo }}$ | - | - | 0.1 | $\mu \mathrm{A}$ |
| Collector Saturation Voltage at $\mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=10 \mathrm{~mA}$ | $\mathrm{V}_{\mathrm{CE}(\text { (sat) }}$ | - | 0.15 | 0.3 | V |
| Gain Bandwidth Product at $\mathrm{V}_{\mathrm{CE}}=6 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}$ | $\mathrm{f}_{T}$ | - | 200 | - | MHz |
| Output Capacitance at $\mathrm{V}_{\mathrm{CB}}=6 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\text {ов }}$ | - | 2.5 | - | pF |
| $\begin{aligned} & \text { Noise Figure } \\ & \text { at } V_{C E}=6 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0.5 \mathrm{~mA} \\ & \mathrm{f}=1 \mathrm{KHz}, \mathrm{R}_{\mathrm{S}}=500 \Omega \end{aligned}$ | NF | - | 4 | - | dB |

